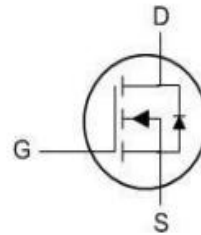
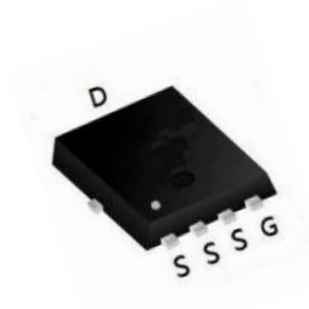


Features

The TW30N06EF is the high cell density trench N-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications. The TW30N06EF meets the RoHS and Green Product requirement, 100%EAS guaranteed with full function reliability approved.

Product Summary

BVDSS	RDSON	ID
60V	24mΩ	30A



PDFN5X6

Maximum Ratings(Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	VDS	60	V
Gate-Source Voltage	VGS	±20	
Continuous Drain Current, VGS @ 10V ^{1.6}	ID@TC =25°C	30	A
Continuous Drain Current, VGS @ 10V ^{1.6}	ID@TC=100°C	15	
Pulsed Drain Current ①	IDM	60	
Single Pulse Avalanche Energy ³	EAS	50	mj
Avalanche Current	I _{AS}	30	A
Power Dissipation ②	PD@TC=25°C	20	W
Storage Temperature	TSTG	-55 to 150	°C
Operating Junction	TJ	-55 to 150	

Thermal Data

Parameter	Symbol	Typ.	Max.	Unit
Thermal Resistance Junction-Ambient	RθJA		62	°C/W

Electrical Characteristics(TJ=25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static Parameters						
Drain-Source Breakdown Voltage	BVDSS	VGS = 0V, ID = 250μA	60			V
Zero Gate Voltage Drain Current	IDSS	VDS = 48V, VGS =0V			1	μA
Gate-Body leakage Current	IGSS	VDS =0V, VGS = ±20V			±100	nA
Gate Threshold Voltage	VGS(th)	VDS =VGS, ID = 250μA	1.2	1.5	2.5	V
Static Drain-Source On-Resistance	RDS(on)	VGS = 10V, ID = 15A		24	30	mΩ
		VGS = 5V, ID = 10A		25	38	mΩ
Dynamic Parameters						
Input Capacitance	Ciss	VDS=15V , VGS=0V , f=1MH		1378		pF
Output Capacitance	Coss			86		pF
Reverse Transfer Capacitance	Crss			64		pF
Total Gate Charge	Qg	VDS=48V , VGS=4.5V , ID=12A		12.6		nC
Gate Source Charge	Qgs			3.2		nC
Gate Drain Charge	Qgd			6.3		nC
Switching Parameters						
Turn-On DelayTime	td(on)	VDD=30V , VGS=10V , RG=3.3Ω, ID=10A		8		ns
Turn-On Rise Time	tr			14.2		ns
Turn-Off DelayTime	td(off)			24.2		ns
Turn-Off Fall Time	tf			4.6		ns
Drain-Source Diode Characteristics and Maximum Ratings						
Diode forward voltage drop.	VSD	VGS=0V , IS=1A , TJ=25℃			1.2	V
Continuous source current	IS	VG=VD=0V , Force Current			30	A
Pulsed source current	ISM				60	

Note :

1. Repetitive Rating : Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t < 10 sec.
3. Pulse Test : Pulse Width≤300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production testing.

Typical Electrical and Thermal Characteristics

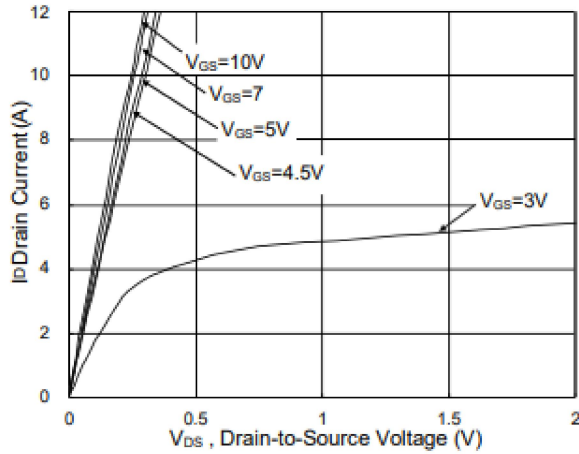


Fig.1 Typical Output Characteristics

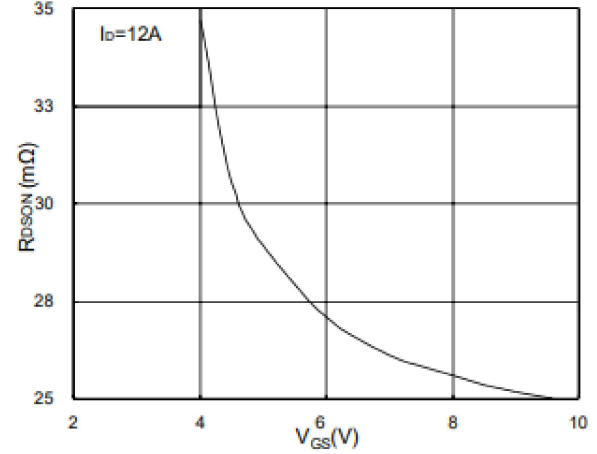


Fig.2 On-Resistance v.s Gate-Source

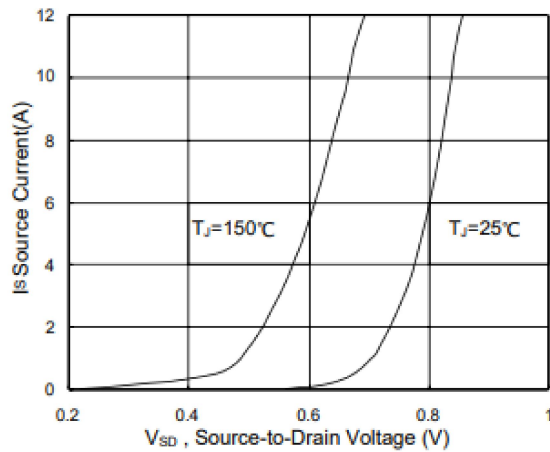


Fig.3 Forward Characteristics of Reverse

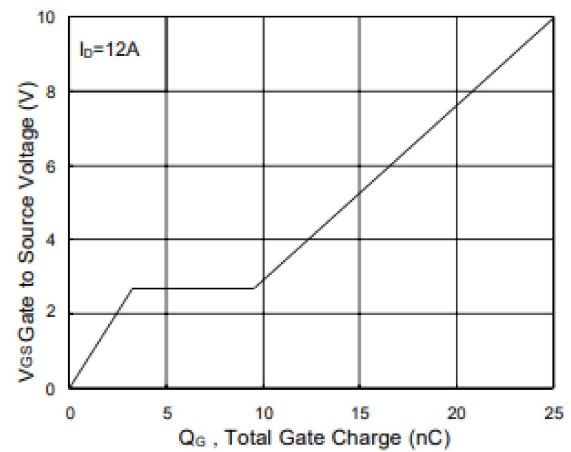


Fig.4 Gate-Charge Characteristics

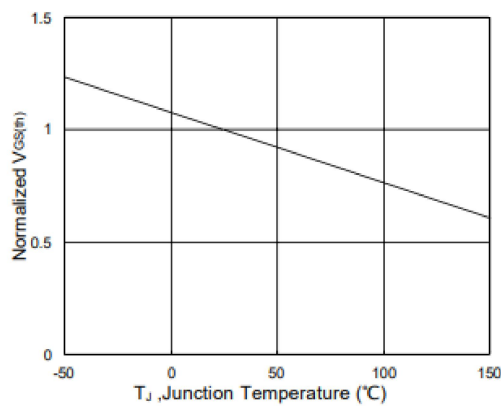


Fig.5 Normalized $V_{GS(th)}$ v.s T_J

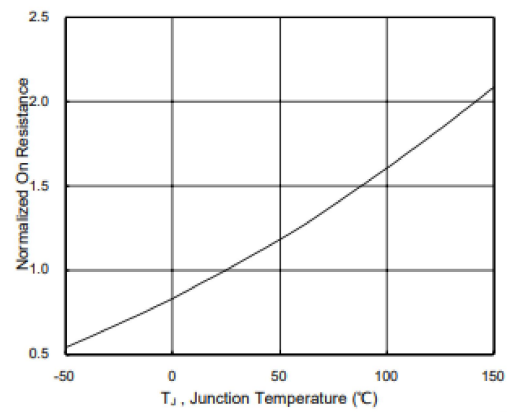


Fig.6 Normalized $R_{DS(on)}$ v.s T_J

Typical Electrical and Thermal Characteristics

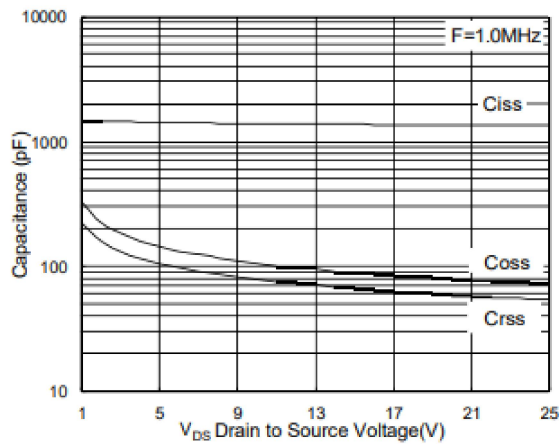


Fig.7 Capacitance

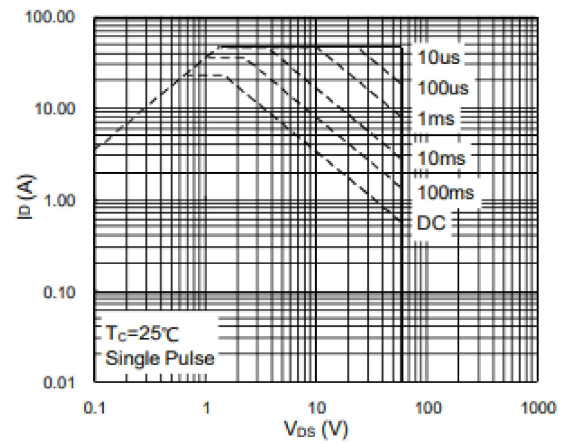


Fig.8 Safe Operating Area

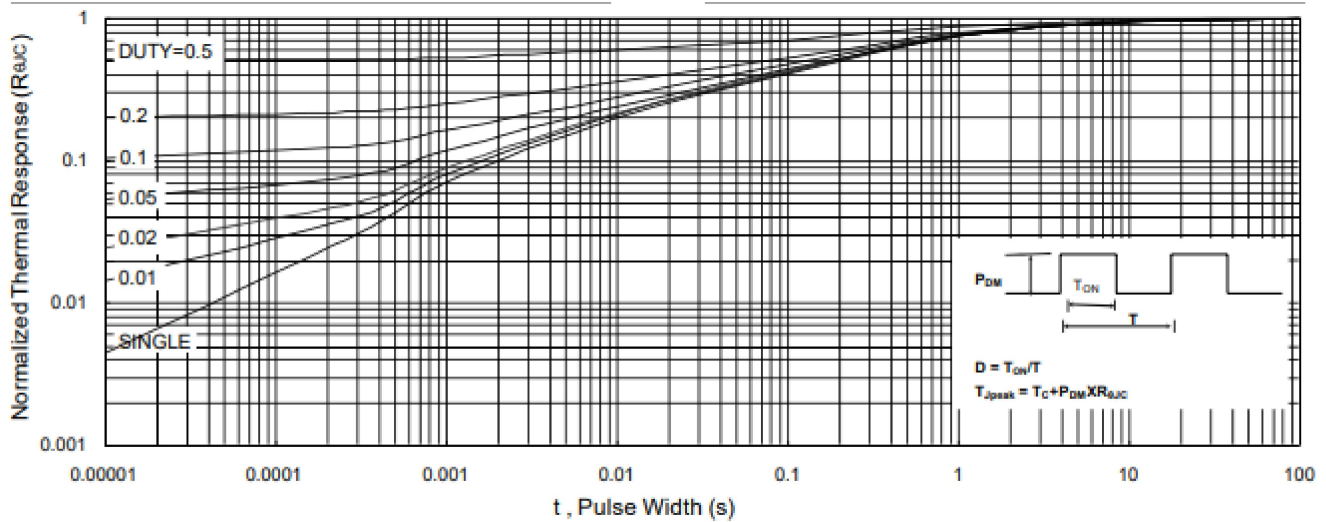


Fig.9 Normalized Maximum Transient Thermal Impedance

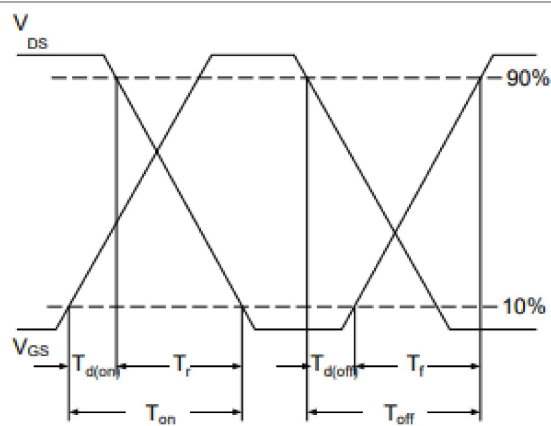


Fig.10 Switching Time Waveform

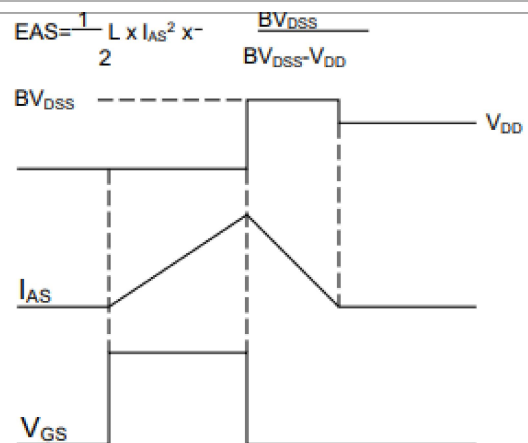
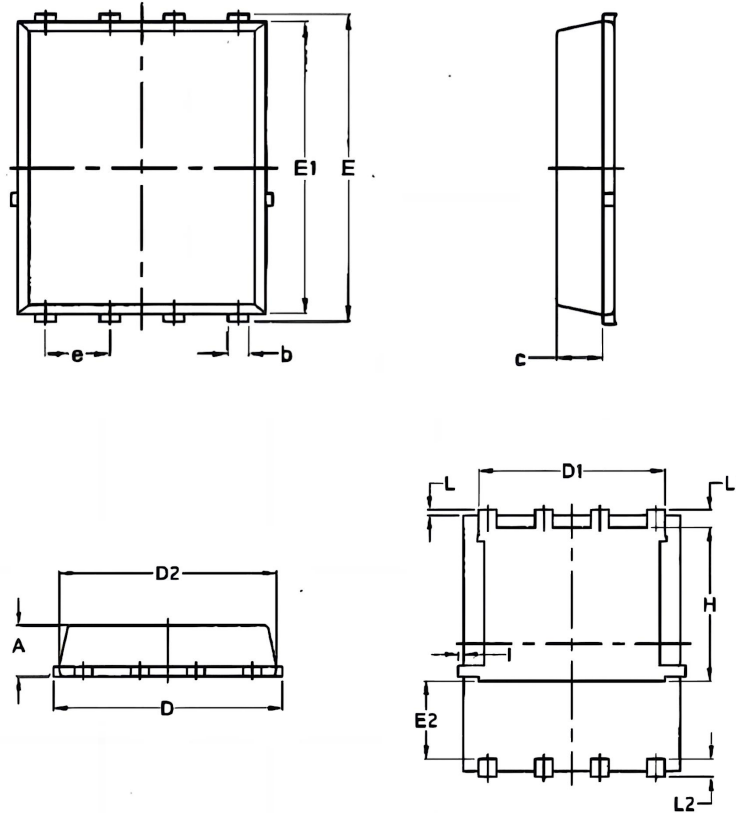


Fig.11 Unclamped Inductive Waveform

PDFN5X6 Package Outline Dimesions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.03	1.17	0.0406	0.0461
b	0.34	0.48	0.0134	0.0189
c	0.824	0.0970	0.0324	0.082
D	4.80	5.40	0.1890	0.2126
D1	4.11	4.31	0.1618	0.1697
D2	4.80	5.00	0.1890	0.1969
E	5.95	6.15	0.2343	0.2421
E1	5.65	5.85	0.2224	0.2303
E2	1.60	/	0.0630	/
e	1.27 BSC		0.05 BSC	
L	0.05	0.25	0.0020	0.0098
L1	0.38	0.50	0.0150	0.0197
L2	0.38	0.50	0.0150	0.0197
H	3.30	3.50	0.1299	0.1378
I	/	0.18	/	0.0070
I	/	0.18	/	0.0070